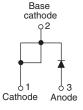


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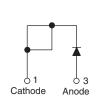
# Ultrafast Rectifier, 15 A FRED Pt<sup>®</sup>



TO-220AC



TO-220 FULL-PAK



VS-15ETX06PbF

VS-15ETX06FPPbF

PRODUCT SUMMARY								
Package	TO-220AC, TO-220FP							
I <sub>F(AV)</sub>	15 A							
V <sub>R</sub>	600 V							
V <sub>F</sub> at I <sub>F</sub>	3.2 V							
t <sub>rr</sub> typ.	18 ns							
T <sub>J</sub> max.	175 °C							
Diode variation	Single die							

### **FEATURES**

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Benchmark ultralow forward voltage drop
- Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

### **DESCRIPTION/APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V					
Average rectified forward current	I=	T <sub>C</sub> = 133 °C	- 15						
Average rectilied for ward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 62 °C (FULL-PAK)	15	А					
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	170	A					
Peak repetitive forward current	I <sub>FM</sub>		30						
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C					

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-					
E	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	2.3	3.2	V				
Forward voltage		I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	1.5	1.8					
Poverse leekage ourrent		V <sub>R</sub> = V <sub>R</sub> rated	-	0.1	50					
Reverse leakage current	I <sub>R</sub>	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	40	300	μA				
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	20	-	pF				
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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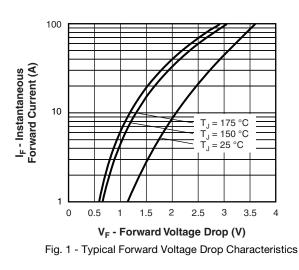
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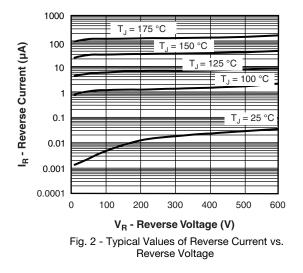
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 \text{ A}, dI_F/dt = 100$	-	18	22					
		$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = 100$	-	20	32					
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	22	-	ns			
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 390 V	-	52	-				
Deal and a second	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.4	-	Α μC			
Peak recovery current		T <sub>J</sub> = 125 °C		-	5.1	-				
	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-				
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	150	-				
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 15 A	-	37	-	ns			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 800 A/µs	-	16	-	А			
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	350	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C			
Thermal resistance,	P		-	1.0	1.3				
junction to case (FULL-PAK)	R <sub>thJC</sub>		-	3.0	3.5				
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W			
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-				
Wainht			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-220AC 15ETX06		FX06					
Marking device		Case style TO-220 FULL-PAK	15ETX06FP						





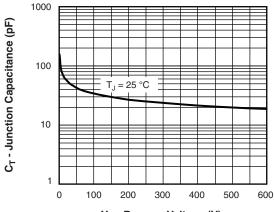
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V<sub>R</sub> - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

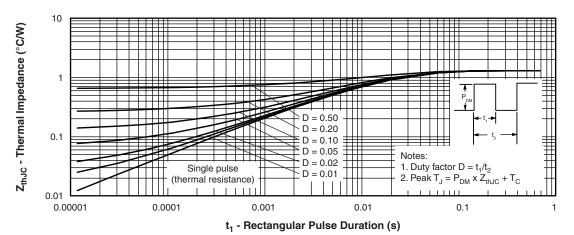


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

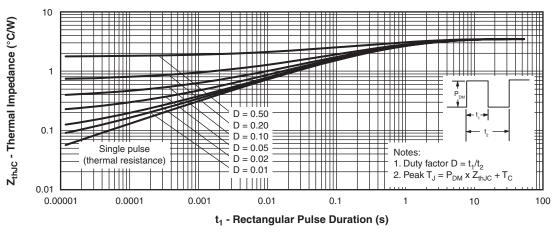


Fig. 5 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (FULL-PAK)

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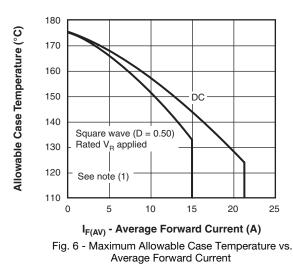
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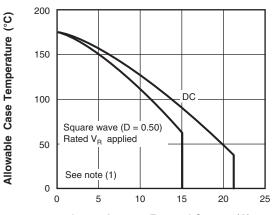
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I<sub>F(AV)</sub> - Average Forward Current (A)

Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

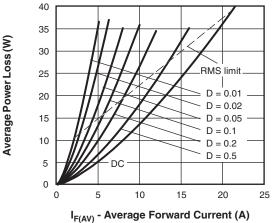
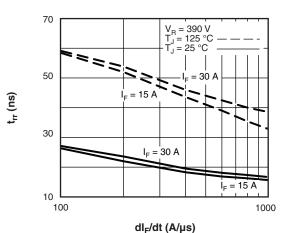


Fig. 8 - Forward Power Loss Characteristics





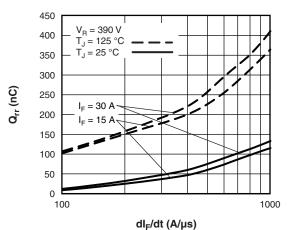


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

Pd = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at ( $I_{F(AV)}/D$ ) (see fig. 8); Pd<sub>REV</sub> = Inverse power loss =  $V_{R1} \times I_R$  (1 - D);  $I_R$  at  $V_{R1}$  = Rated  $V_R$ 

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VS-15ETX06PbF, VS-15ETX06FPPbF

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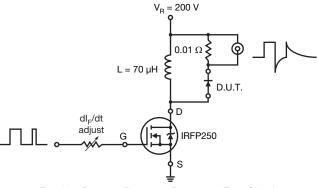
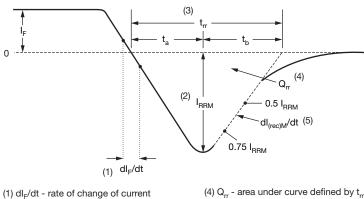


Fig. 11 - Reverse Recovery Parameter Test Circuit



through zero crossing

and I<sub>RRM</sub>

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ 

(2) I<sub>RRM</sub> - peak reverse recovery current

(3) t<sub>rr</sub> - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.

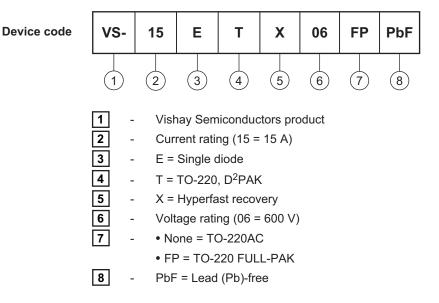
(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

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## ORDERING INFORMATION TABLE



Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS								
Dimensions	TO-220AC	www.vishay.com/doc?95221						
	TO-220AC FULL-PAK	www.vishay.com/doc?95005						
Part marking information	TO-220AC	www.vishay.com/doc?95224						
	TO-220AC FULL-PAK	www.vishay.com/doc?95009						

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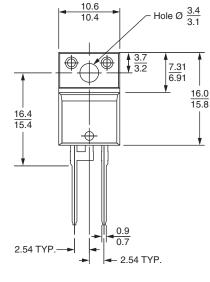
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# **Outline Dimensions**

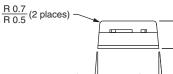
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## **DIMENSIONS** in millimeters

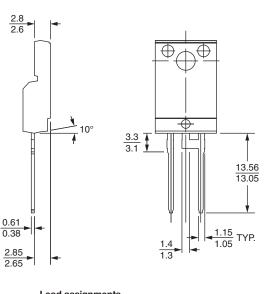


 $\frac{4.8}{4.6}$ 

 $5^{\circ} \pm 0.5^{\circ}$ 



 $5^{\circ} \pm 0.5^{\circ}$ 



Lead assignments Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



**Vishay Semiconductors** 

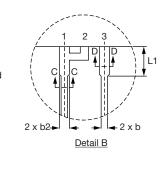
**TO-220AC** 

plane

### **DIMENSIONS** in millimeters and inches









**Diodes** 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
С	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØΡ	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Dimension b1, b3 and c1 apply to base metal only
- <sup>(5)</sup> Controlling dimension: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1
- <sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- <sup>(8)</sup> Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

Document Number: 95221 Revision: 07-Mar-11

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